BTA2008 series D and E

0.8 A Three-quadrant triacs high commutation

Rev. 01 — 18 January 2008 Product data sheet

1. Product profile

1.1 General description

Passivated, guaranteed commutation, sensitive gate triacs in a SOT54 plastic package

1.2 Features

- Guaranteed commutation performance at each gate sensitivity
- Sensitive gate
- Easily interfaced with low power drivers including microcontrollers

1.3 Applications

- Motor control
- Solenoid drivers

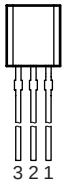
1.4 Quick reference data

- $V_{DRM} \leq 600$ V (BTA2008-600D)
- $V_{DRM} \leq 600$ V (BTA2008-600E)
- $V_{DRM} \leq 800$ V (BTA2008-800D)
- $V_{DRM} \leq 800$ V (BTA2008-800E)
- $I_{TSM} \leq 9$ A (t = 20 ms)
- $I_{GT} \leq 5$ mA (BTA2008-600D)
- $I_{GT} \leq 5$ mA (BTA2008-800D)
- $I_{GT} \leq 10$ mA (BTA2008-600E)
- $I_{GT} \leq 10$ mA (BTA2008-800E)
- $I_{T(RMS)} \leq 0.8$ A

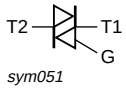
2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 2 (T2)		
2	gate (G)		
3	main terminal 1 (T1)		



SOT54 (TO-92)



3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BTA2008-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BTA2008-600E			
BTA2008-800D			
BTA2008-800E			

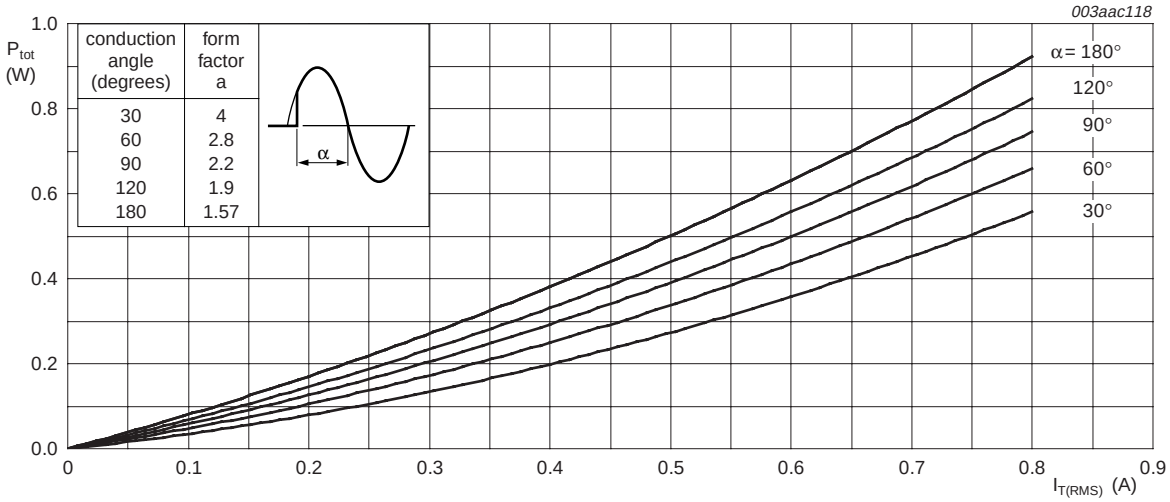
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

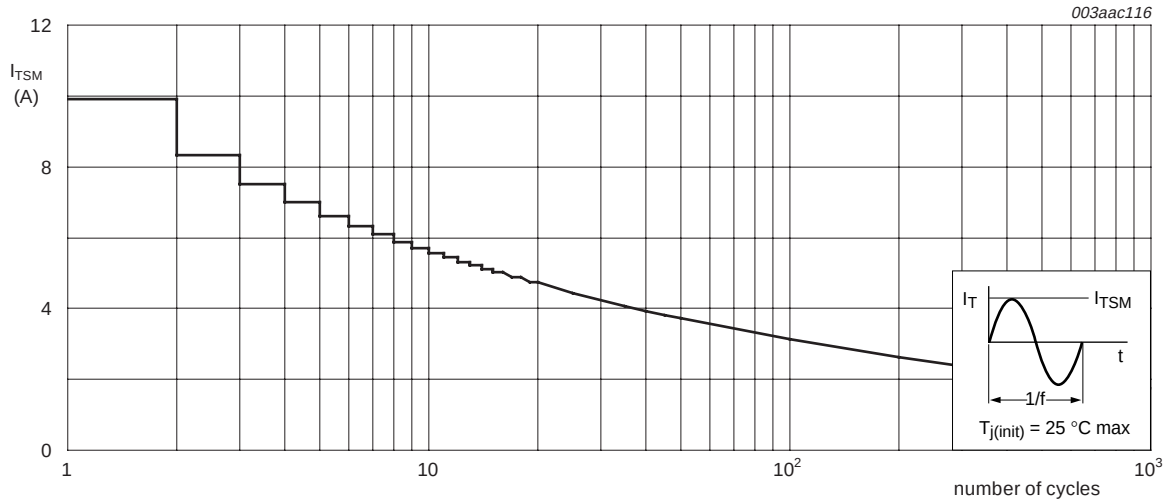
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA2008-600D; BTA2008-600E	[1]	-	600	V
		BTA2008-800D; BTA2008-800E		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 70$ °C; see Figure 4 and 5		-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3				
		t = 20 ms		-	9	A
		t = 16.7 ms		-	9.9	A
I^2t	I^2t for fusing	$t_p = 10$ ms		-	0.41	A^2s
dI_T/dt	rate of rise of on-state current	$I_{TM} = 1.5$ A; $I_G = 20$ mA; $dI_G/dt = 0.2$ A/µs		-	100	A/µs
I_{GM}	peak gate current			-	1	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			–40	+150	°C
T_j	junction temperature			-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/µs.



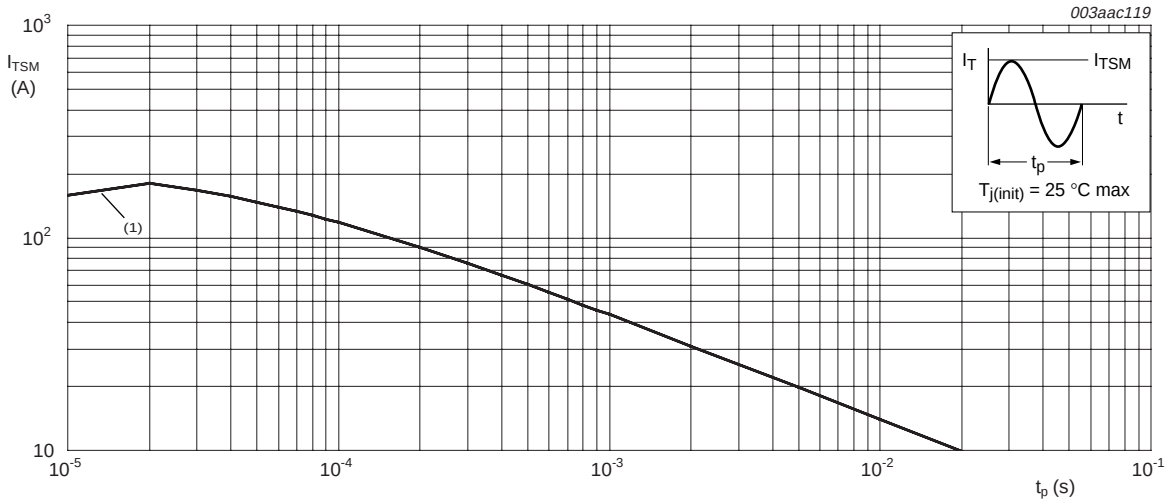
α = conduction angle

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

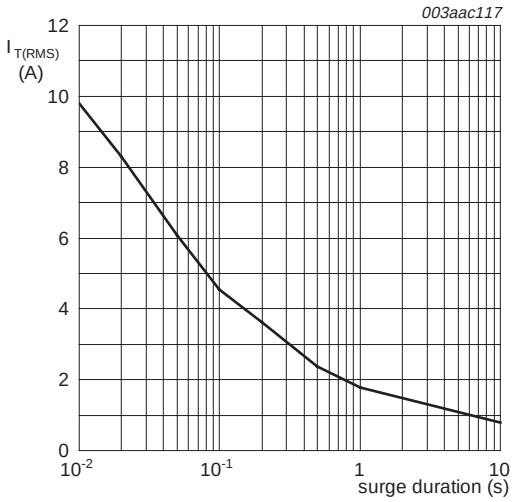
Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$ ms

(1) dI_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values



f = 50 Hz

T_{lead} = 70 °C

Fig 4. RMS on-state current as a function of surge duration; maximum values

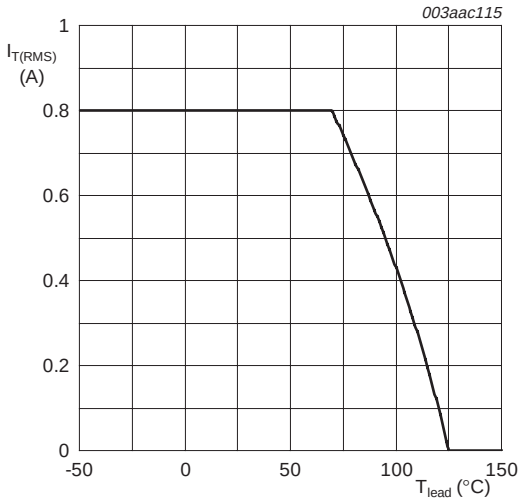


Fig 5. RMS on-state current as a function of lead temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	printed circuit board mounted; lead length 4 mm	-	150	-	K/W

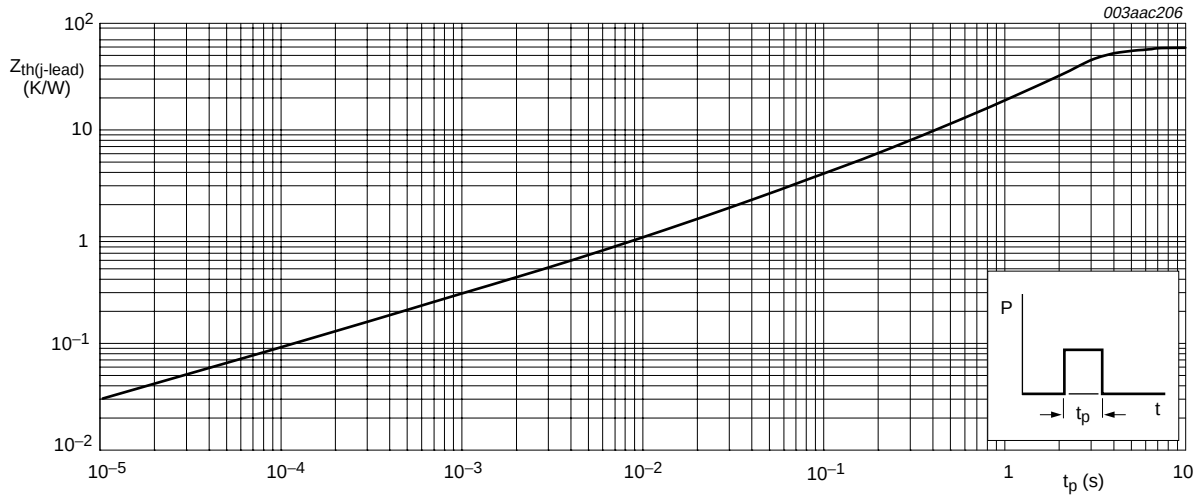


Fig 6. Transient thermal impedance from junction to lead as a function of pulse duration

6. Static characteristics

Table 5. Static characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	BTA2008-600D BTA2008-800D			BTA2008-600E BTA2008-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; see Figure 8							
		T2+ G+	0.25	-	5	0.5	-	10	mA
		T2+ G–	0.25	-	5	0.5	-	10	mA
		T2– G–	0.25	-	5	0.5	-	10	mA
I_L	latching current	V_D = 12 V; I_{GT} = 0.1 A; see Figure 10							
		T2+ G+	-	-	10	-	-	12	mA
		T2+ G–	-	-	20	-	-	20	mA
		T2– G–	-	-	10	-	-	12	mA
I_H	holding current	V_D = 12 V; I_{GT} = 0.1 A; see Figure 11	-	-	10	-	-	12	mA
V_T	on-state voltage	I_T = 0.85 A; see Figure 9	-	1.35	1.6	-	1.35	1.6	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; see Figure 7	-	0.9	2	-	0.9	2	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C	0.2	0.3	-	0.2	0.3	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; T_j = 125 °C	-	0.1	0.5	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	BTA2008-600D BTA2008-800D			BTA2008-600E BTA2008-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; T_j = 125 °C; exponential waveform; gate open circuit	200	-	-	600	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_{DM} = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV/dt = 10 V/µs; gate open circuit	0.5	-	-	1.6	-	-	A/ms
t_{gt}	gate-controlled turn-on time	I_{TM} = 1 A; $V_D = V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	-	2	-	µs

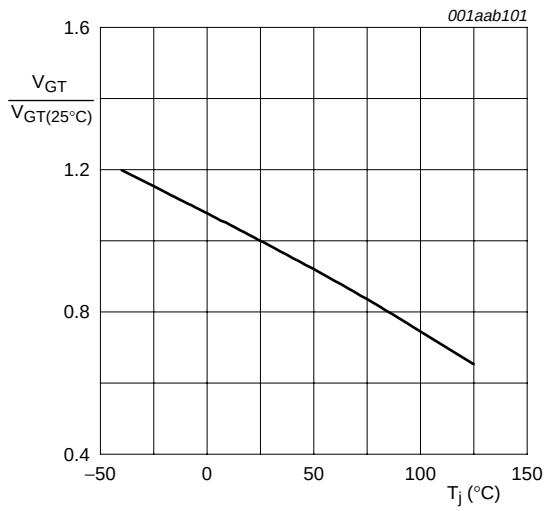
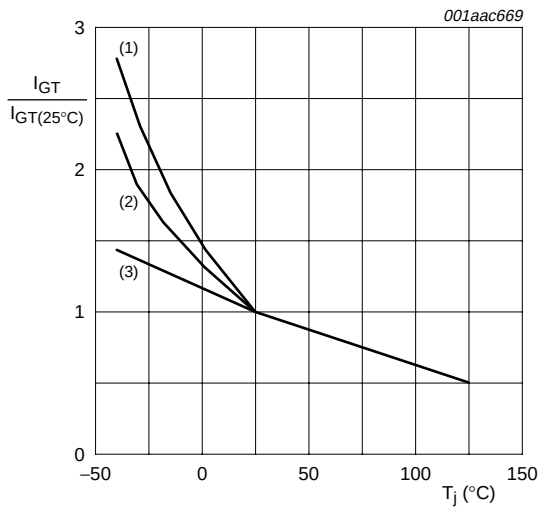
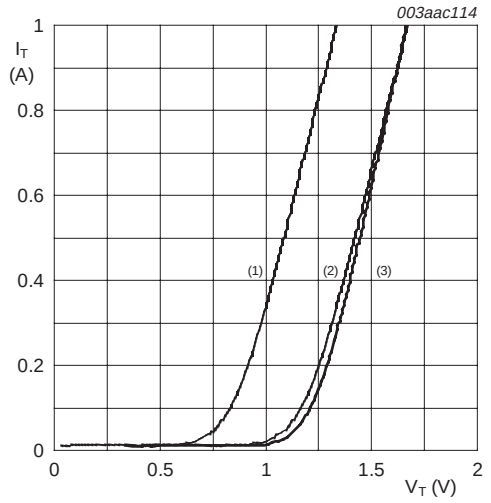


Fig 7. Normalized gate trigger voltage as a function of junction temperature



(1) T2– G–
(2) T2+ G–
(3) T2+ G+

Fig 8. Normalized gate trigger current as a function of junction temperature



V_o = 0.835 V

R_s = 0.5 Ω

(1) T_j = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) T_j = 25 °C; maximum values

Fig 9. On-state current as a function of on-state voltage

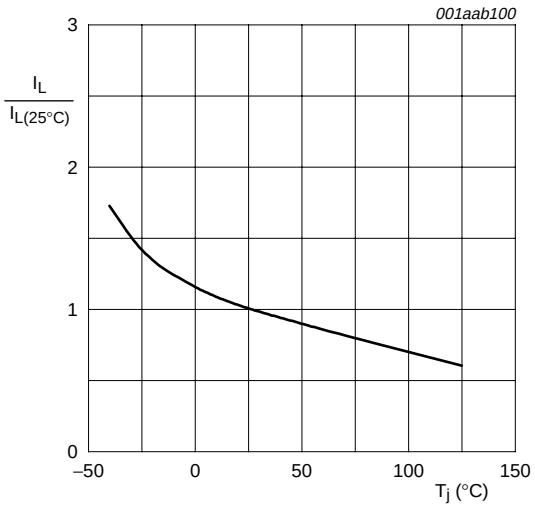


Fig 10. Normalized latching current as a function of junction temperature

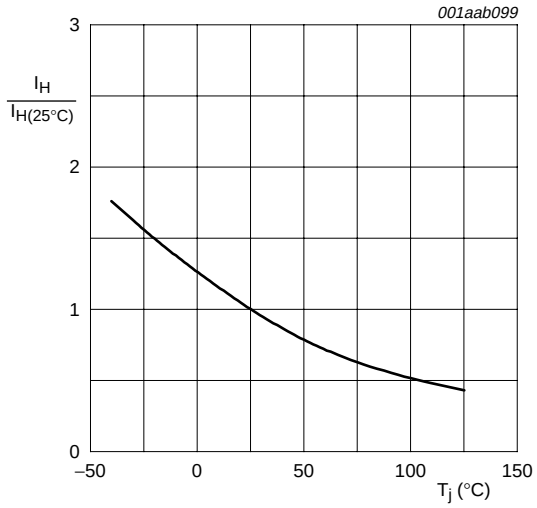
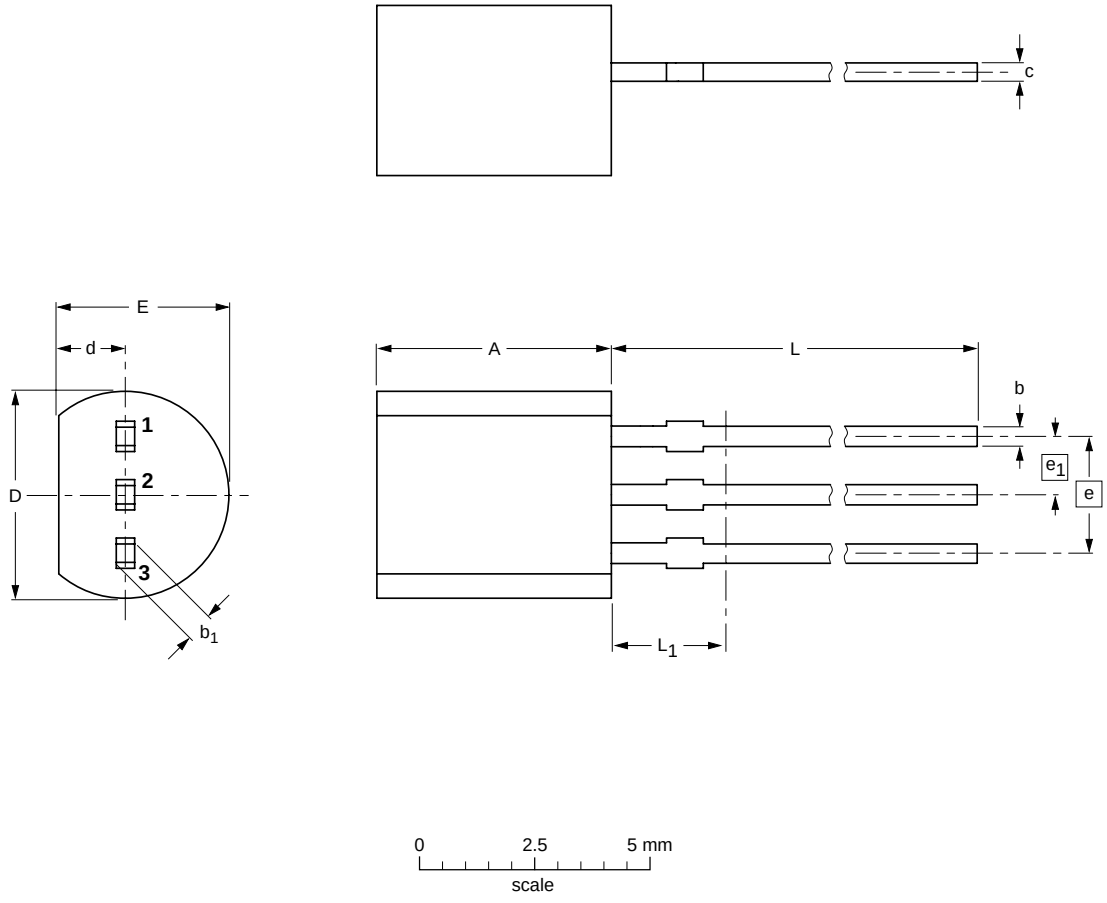


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1 (1) max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			~~04-06-28~~ 04-11-16

Fig 12. Package outline SOT54 (TO-92)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA2008_SER_D_E_1	20080118	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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12. Contents

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